Product data sheet

1. General description

Planar passivated very sensitive gate four quadrant triac in a SOT223 surface-mountable plastic package intended for applications requiring direct interfacing to logic level ICs and low power gate drivers.

2. Features and benefits

- Direct interfacing to logic level ICs
- · Direct interfacing to low power gate drive circuits
- High blocking voltage capabiliy
- Planar passivated for voltage ruggedness and reliability
- Surface-mountable package
- · Triggering in all four quadrants
- Very sensitive gate in four quadrants

3. Applications

- General purpose low power motor control
- Home appliances
- Industrial process control
- Low power AC Fan controllers

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Absolute	maximum rating					
V_{DRM}	repetitive peak off-state voltage		-	-	600	V
I _{T(RMS)}	RMS on-state current	full sine wave; $T_{sp} \le 105 ^{\circ}\text{C}$; Fig. 1; Fig. 2; Fig. 3	-	-	1	А
I _{TSM}	non-repetitive peak on- state current	full sine wave; $T_{j(init)}$ = 25 °C; t_p = 20 ms; Fig. 4; Fig. 5	-	-	8	А
		full sine wave; $T_{j(init)} = 25 \text{ °C}$; $t_p = 16.7 \text{ ms}$	-	-	8.5	А
T _j	junction temperature		-	-	125	°C
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static ch	aracteristics					
I _{GT}	gate trigger current	$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2 + G+;$ $T_j = 25 \text{ °C; } Fig. 9$	-	-	3	mA
		$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2 + \text{ G-;} $ $T_j = 25 \text{ °C; } Fig. 9$	-	-	3	mA

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Symbol	Parameter	Conditions		Min	Тур	Max	Unit	
Static cha	Static characteristics							
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2- \text{ G-};$ $T_j = 25 \text{ °C}; Fig. 9$		-	-	3	mA	
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2- G+; $ $T_j = 25 \text{ °C}; Fig. 9$		-	-	5	mA	
I _H	holding current	V _D = 12 V; T _j = 25 °C; <u>Fig. 11</u>		-	-	7	mA	
V _T	on-state voltage	I _T = 1.4 A; T _j = 25 °C; <u>Fig. 12</u>		-	1.3	1.6	V	
Dynamic	characteristics							
dV _D /dt	rate of rise of off-state voltage	V_{DM} = 402 V; T_j = 110 °C; (V_{DM} = 67% of V_{DRM}); exponential waveform; gate open circuit; Fig. 14		10	-	-	V/µs	
dV _{com} /dt	rate of change of commutating voltage	$V_D = 400 \text{ V}; T_j = 110 ^{\circ}\text{C};$ $dI_{com}/dt = 0.44 \text{ A/ms}; gate open circuit}$		0.5	-	-	V/µs	

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	T1	main terminal 1		Z
2	T2	main terminal 2		T2 T1
3	G	gate		sym051
4	T2	main terminal 2	1 2 3	

6. Ordering information

Table 3. Ordering information

Type number	Package Name	Orderable part number	Packing method	Small packing quantity	Package version	Package issue date
Z0103MN	SOT223	Z0103MN,135	Reel	4000	SOT223	16-Mar-2006

7. Marking

Table 4. Marking codes

Type number	Marking codes			
	Assembly factory: d	Assembly factory: L		
Z0103MN	Jdxxx 0103MN	JLxxx 0103MN		

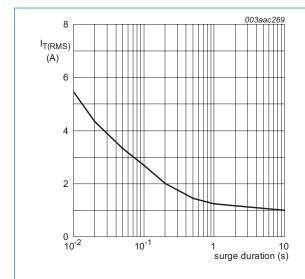
8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DRM}	repetitive peak off-state voltage [1]		-	600	V
I _{T(RMS)}	RMS on-state current	full sine wave; $T_{sp} \le 105 ^{\circ}\text{C}$; Fig 1; Fig 2; Fig 3	-	1	А
I _{TSM}	non-repetitive peak on- state current	full sine wave; $T_{j(init)} = 25 \text{ °C}$; $t_p = 20 \text{ ms}$; Fig 4; Fig 5	-	8	А
		full sine wave; $T_{j(init)}$ = 25 °C; t_p = 16.7 ms	-	8.5	А
l ² t	I ² t for fusing	t _p = 10 ms; SIN	-	0.32	A ² s
dl _T /dt	rate of rise of on-state current	I _G = 20 mA; T2+ G+	-	50	A/µs
		I _G = 20 mA; T2+ G-	-	50	A/µs
		I _G = 20 mA; T2- G-	-	50	A/µs
		I _G = 20 mA; T2- G+	-	20	A/µs
I _{GM}	peak gate current		-	1	А
P_GM	peak gate power		-	2	W
P _{G(AV)}	average gate power	over any 20 ms period	-	0.1	W
T _{stg}	storage temperature		-40	150	°C
T _j	junction temperature		-	125	°C

[1] Although not recommended, off-state voltage up to V_{DRM} may be applied without damage, but the triac may switch to the on-state. The rate of rise of current should not exceed $3A/\mu s$.



f = 50 Hz; T_{sp} = 105 °C Fig. 1. RMS on-state current as a function of surge duration; maximum values

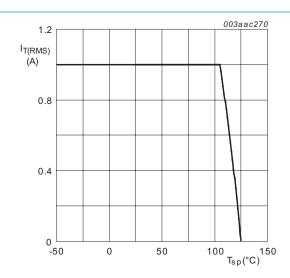
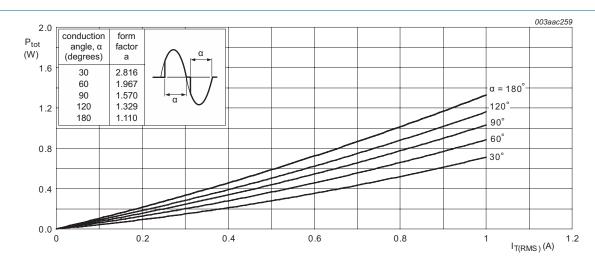


Fig. 2. RMS on-state current as a function of solder point temperature; maximum values



 α = conduction angle

a = form factor = $I_{T(RMS)} / I_{T(AV)}$

Fig. 3. Total power dissipation as a function of RMS on-state current; maximum values

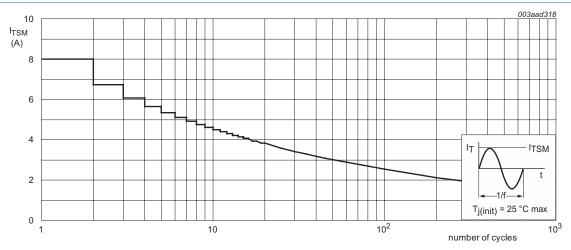
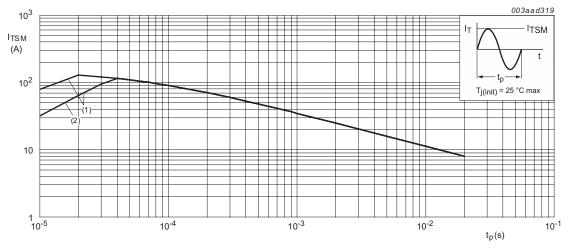


Fig. 4. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values



 $t_p \le 20 \text{ ms}$

Z0103MN

 $(1) dI_T/dt limit$

(2) T2- G+ quadrant limit

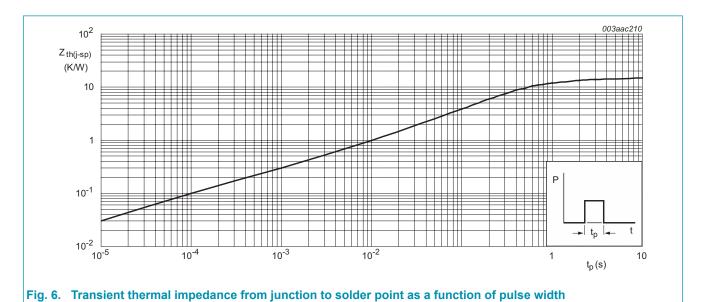
Fig. 5. Non-repetitive peak on-state current as a function of pulse width; maximum values

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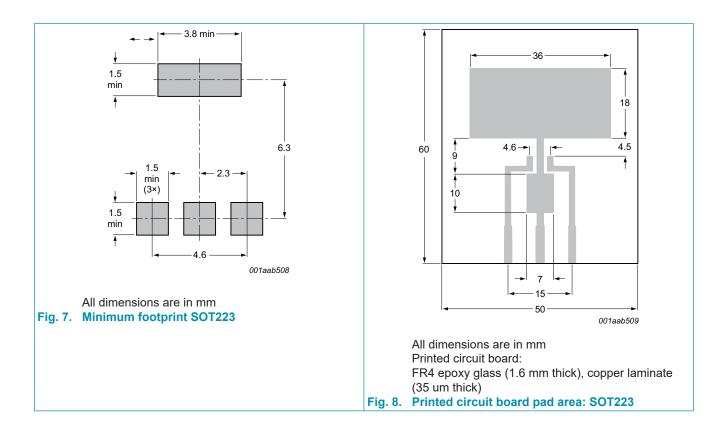
9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{\text{th(j-sp)}}$	thermal resistance from junction to solder point	full cycle; Fig 6	-	-	15	K/W
$R_{\text{th(j-a)}}$	thermal resistance from junction to	full cycle; printed circuit board mounted; minimum footprint; <u>Fig 7</u>	-	156	-	K/W
	ambient	full cycle; printed circuit board mounted; pad area; Fig 8	-	70	-	K/W



4Q Triac

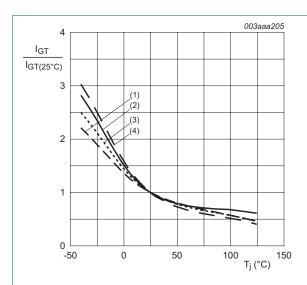


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10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	aracteristics				,	
I _{GT} gate trigger c	gate trigger current	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2+ G+; $ $T_j = 25 \text{ °C}; Fig. 9$	-	-	3	mA
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2+ \text{ G-};$ $T_j = 25 \text{ °C}; Fig. 9$	-	-	3	mA
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2- \text{ G-};$ $T_j = 25 \text{ °C}; Fig. 9$	-	-	3	mA
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2- G+; $ $T_j = 25 \text{ °C}; Fig. 9$	-	-	5	mA
I _L	latching current	$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; T2+ G+;$ $T_j = 25 \text{ °C}; Fig. 10$	-	-	7	mA
		$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; T2+ G-;$ $T_j = 25 \text{ °C}; Fig. 10$	-	-	15	mA
		$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; T2- \text{ G-};$ $T_j = 25 \text{ °C}; Fig. 10$	-	-	7	mA
		$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; T2- \text{ G+};$ $T_j = 25 \text{ °C}; Fig. 10$	-	-	7	mA
I _H	holding current	V _D = 12 V; T _j = 25 °C; <u>Fig. 11</u>	-	-	7	mA
V _T	on-state voltage	I _T = 1.4 A; T _j = 25 °C; <u>Fig. 12</u>	-	1.3	1.6	V
V_{GT}	gate trigger voltage	V _D = 12 V; I _T = 0.1 A; T _j = 25 °C; Fig. 13	-	-	1	V
		V _D = 600 V; I _T = 0.1 A; T _j = 125 °C	0.2	-	-	V
I _D	off-state current	V _D = 600 V; T _j = 125 °C	-	-	0.5	mA
Dynamic	characteristics					
dV _D /dt	rate of rise of off-state voltage	V_{DM} = 402 V; T_j = 110 °C; (V_{DM} = 67% of V_{DRM}); exponential waveform; gate open circuit; Fig. 14	10	-	-	V/µs
dV _{com} /dt	rate of change of commutating voltage	$V_D = 400 \text{ V}; T_j = 110 ^{\circ}\text{C};$ $dI_{com}/dt = 0.44 \text{ A/ms}; \text{ gate open circuit}$	0.5	-	-	V/µs





- (2) T2- G-
- (3) T2+ G-
- (4) T2+ G+

Fig. 9. Normalized gate trigger current as a function of junction temperature

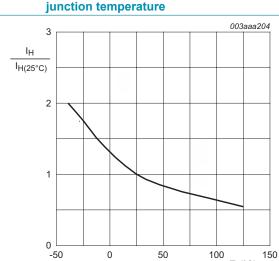


Fig. 11. Normalized holding current as a function of junction temperature

T_i (°C)

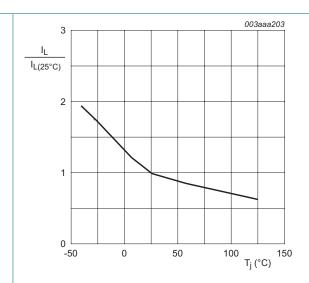
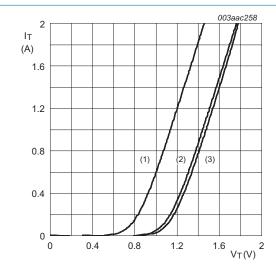


Fig. 10. Normalized latching current as a function of junction temperature



 $V_o = 1.13 \text{ V}; R_s = 0.31 \Omega$

(1) T_j = 125 °C; typical values (2) T_j = 125 °C; maximum values

(3) T_i = 25 °C; maximum values

Fig. 12. On-state current as a function of on-state voltage

4Q Triad

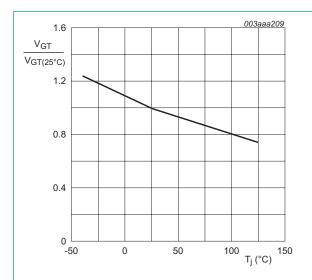


Fig. 13. Normalized gate trigger voltage as a function of junction temperature

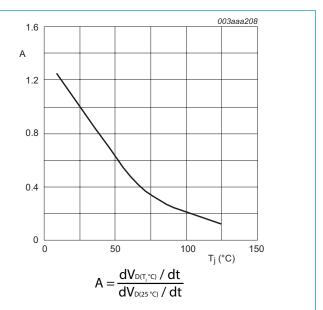
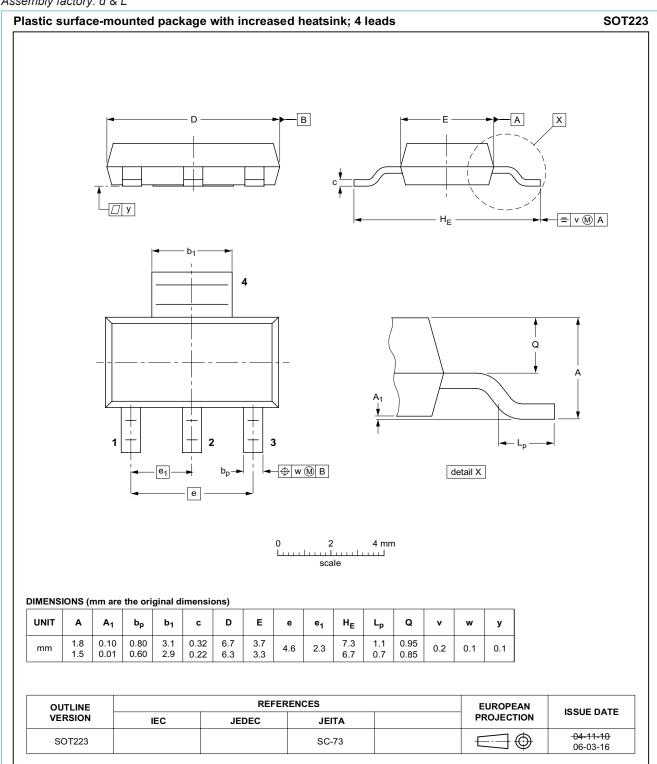


Fig. 14. Normalized critical rate of rise of off-state voltage as a function of junction temperature; typical values

11. Package outline

Assembly factory: d & L



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12. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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